

U.S. Patent Application Serial No. **10/041,609**
Amendment dated September 11, 2003
Reply to OA of **April 23, 2003**

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims:

1-17 (Canceled)

18. (Currently amended): Semiconductor device having comprising:
a semiconductor substrate having an underlying semiconductor surface;
an insulator film deposited on said underlying semiconductor surface, said insulator film forming a
semiconductor-insulator junction obtained by depositing an insulator film on an underlying semiconductor
surface,

wherein the interfacial level density of said semiconductor-insulator junction is $10^{12} \text{ eV}^{-1}\text{cm}^{-2}$ or less
as a result that, and

said insulator film is deposited on said underlying semiconductor surface after a treatment that
reduces interfacial defects on said semiconductor-insulator junction utilizing a reaction of a treatment gas
supplied ~~with~~ to the semiconductor substrate having said underlying semiconductor surface via a thermal
catalysis body provided near said substrate.

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19. (Previously presented): Semiconductor device as claimed in claim 18, wherein said semiconductor-insulation junction is one obtained by deposition of said insulator film, which is carried out in said same process chamber after said treatment and utilizes a reaction of a deposition gas supplied with said substrate via said same thermal catalysis body.